Dual N-Channel 20 V (D-S) 175 °C MOSFET

DESCRIPTION

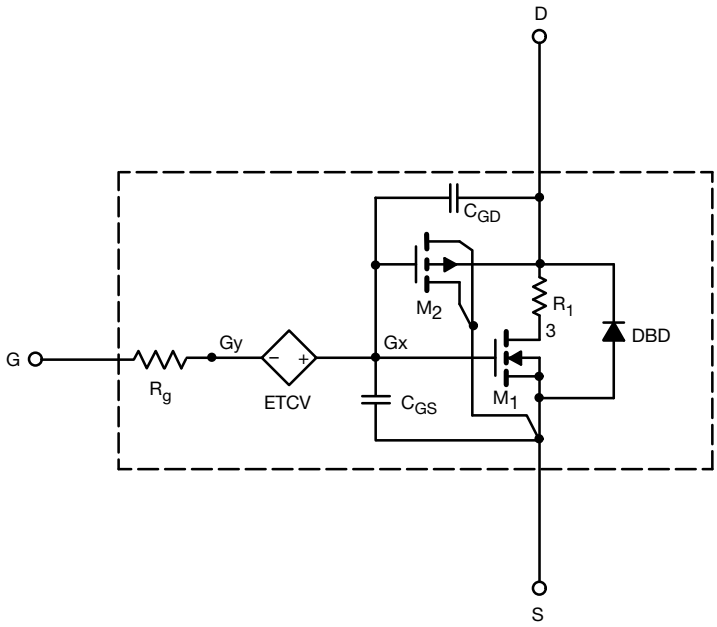
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The sub-circuit model is extracted and optimized over the -55 °C to +125 °C temperature ranges under the pulsed 0 V to 5 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Sub-circuit Model)
- Level 3 MOS
- Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- Model the Gate Charge

SUBCIRCUIT MODEL SCHEMATIC



Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.

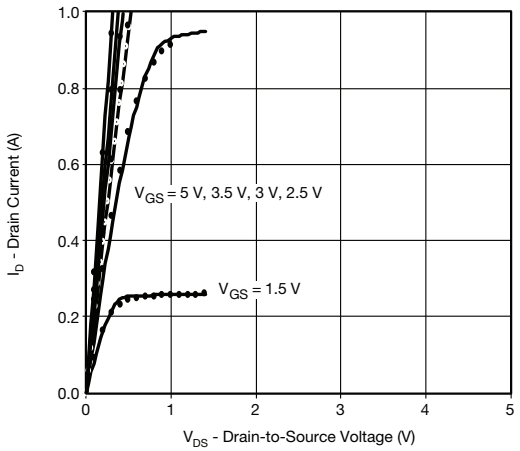
SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)					
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**SIMULATED DATA**	**MEASURED DATA**	**UNIT**
Static					
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	0.91	-	V
Drain-Source On-State Resistance [a]	$R_{DS(on)}$	V_{GS} = 4.5 V, I_D = 0.66 A	0.324	0.345	Ω
		V_{GS} = 2.5 V, I_D = 0.4 A	0.495	0.482	
Forward Transconductance [a]	g_{fs}	V_{DS} = 10 V, I_D = 1 A	1.5	1.1	S
Diode Forward Voltage	V_{SD}	I_S = 0.5 A	0.80	0.85	V
Dynamic [b]					
Input Capacitance	C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	62	61	pF
Output Capacitance	C_{oss}		20	20	
Reverse Transfer Capacitance	C_{rss}		11	11	
Total Gate Charge	Q_g	V_{DS} = 10 V, V_{GS} = 4.5 V, I_D = 1.2 A	0.60	0.83	nC
Gate-Source Charge	Q_{gs}		0.12	0.12	
Gate-Drain Charge	Q_{gd}		0.23	0.23	

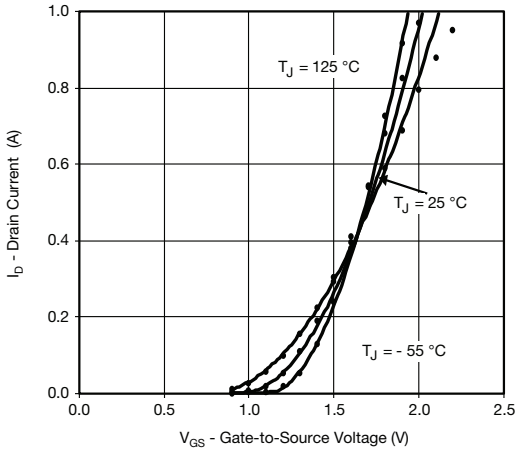
Notes

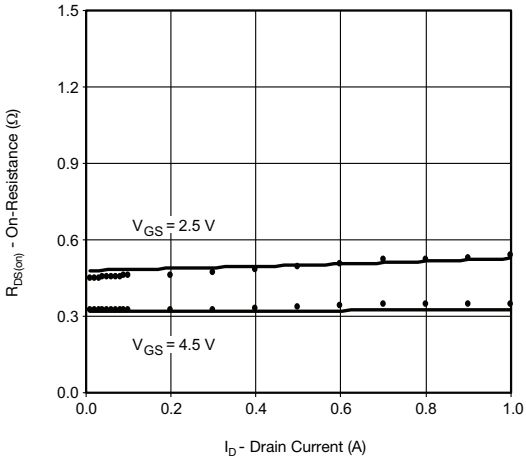
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

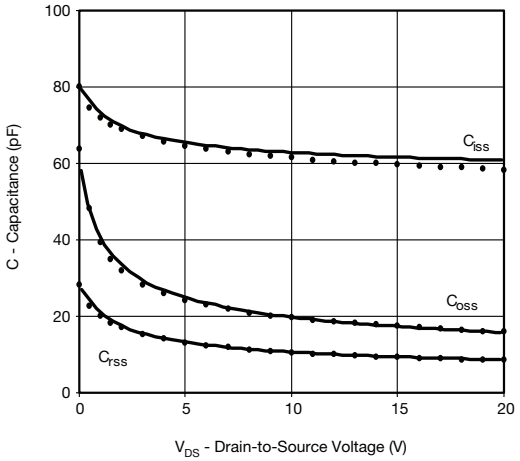
b. Guaranteed by design, not subject to production testing.

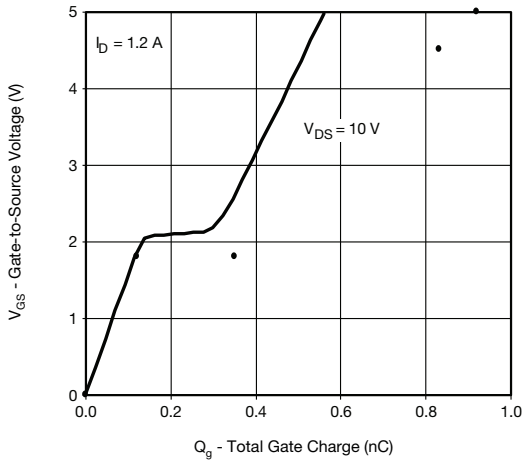
COMPARISON OF MODEL WITH MEASURED DATA (T_J = 25 °C, unless otherwise noted)

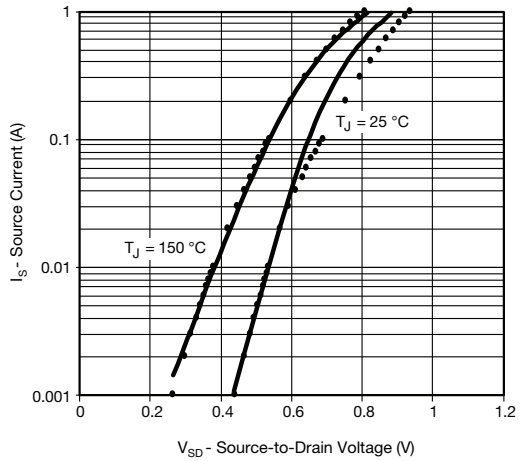












Note

- Dots and squares represent measured data.